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(54) Title: MICROELECTRONICS PACKAGE ASSEMBLIES AND PROCESSES FOR MAKING

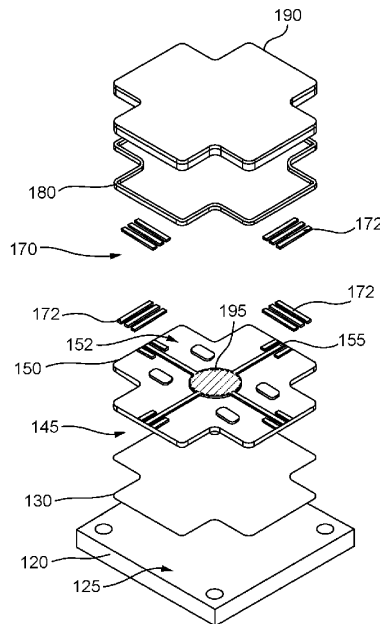


FIG. 2

(57) Abstract: A microelectronics package assembly and process of making same are disclosed. The flange has an upper surface and a first coating disposed on the upper surface of the flange. The insulator has a bottom surface for mounting onto the flange and an upper surface opposite the bottom surface. A second coating is disposed on the bottom surface of the insulator and a third coating disposed on the upper surface of the insulator. The first coating, the second coating, and the third coating each have a thickness of less than or equal to 1 micron. At least one of the first coating, the second coating, and the third coating is applied via at least one of physical vapor deposition, atomic deposition, or chemical deposition.

[Continued on next page]

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